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# Australian Standard<sup>®</sup> 2547.1.8—1986

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## SEMICONDUCTOR DEVICES— Part 1.8—DISCRETE DEVICES— FIELD-EFFECT TRANSISTORS



**STANDARDS ASSOCIATION OF AUSTRALIA**  
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This Australian standard was prepared by Committee TE/12, Semiconductors and Devices. It was approved on behalf of the Council of the Standards Association of Australia on 24 April 1986 and published on 4 August 1986.

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The following interests are represented on Committee TE/12:

Department of Defence

Department of Industry, Technology and Commerce

Confederation of Australian Industry

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Telecom Australia

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AUSTRALIAN STANDARD

**SEMICONDUCTOR DEVICES—  
Part 1.8  
DISCRETE DEVICES—  
FIELD-EFFECT TRANSISTORS**

**AS 2547.1.8—1986**

First published .....1986

*see also Preface (p.2) and  
cross references index (p.5)*

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## PREFACE

This standard was prepared by the Association's Committee on Semiconductors and Devices. It is reproduced from IEC 747.8:1984 and is one of the standards prepared by IEC/TC 47, Semiconductor Devices.

This standard is one of a series of standards published under the generic specification AS 2547. This standard supersedes:

- the existing AS 2547 series (published in 1982 and 1983 and identical to equivalent parts of IEC 147 published between 1966 and 1981);
- AS C366, Part 4—1978 and Part 5—1978 (equivalent to IEC 147-4, IEC 147-5 and IEC 147-5A);
- AS C367 (endorsement of IEC 148—1969);
- AS 1967 (identical to IEC 147-1D and 1E).

The purpose of IEC 747 is to reorganize into a device oriented publication, the material originally presented in the IEC 147\* series and IEC 148† on semiconductor devices and letter symbols representing them is now republished as follows:

- (a) Specific requirements for integrated circuits—now IEC 748.
- (b) Mechanical and climatic test methods—now IEC 749.

It was in view of the above reorganization that Committee TE/12 agreed to integrate the entire series into one series of Australian standards using the generic designation AS 2547. The relationship with the three IEC standards is as follows:

- (i) Part 1.1 onwards—identical with the IEC 747 series.
- (ii) Part 2.1 onwards—identical with the IEC 748 series.
- (iii) Part 3.1—identical with IEC 749.

For the purpose of this Australian standard and all other standards in this AS 2547 series, the text of the reproduced IEC Publications should be modified as follows:

- A. *Terminology.* The words 'Australian Standard' should replace the words 'IEC Publication' wherever they appear.
- B. *Cross-references.* The reference to IEC Publications should be replaced by references to the appropriate Australian Standards as follows:

<i>Reference to IEC Publications</i>		<i>Appropriate Australian Standard</i>	
IEC 27	Letter symbols to be used in electrical technology	AS 1046	Letter Symbols for Use in Electrotechnology
IEC 50	International Electrotechnical Vocabulary	AS 1852	International Electrotechnical Vocabulary
IEC 191	Mechanical standardization of semiconductor devices	AS C379	Mechanical Standardization of Semiconductor Devices
IEC 319	Presentation of reliability data on electronic components	AS 2350	Presentation of Reliability Data on Electronic and Similar Components
IEC 747	Semiconductor devices. Discrete devices and integrated circuits	AS 2547	Semiconductor Devices
747.1	Part 1—General	1.1	Discrete Devices—General
747.2	Part 2—Rectifier diodes	1.2	Discrete Devices—Rectifier Diodes
747.3	Signal (including switching) and regulator diodes	1.3	Discrete Devices—Signal (Including Switching) and Regulator Diodes
747.4	R.F. Diodes	1.4	Discrete Devices—R.F. Diodes
747.5	Optoelectronic devices	1.5	Discrete Devices—Optoelectronic Devices
747.6	Thyristors	1.6	Discrete Devices—Thyristors

\* IEC 147, Essential ratings and characteristics of semiconductor devices and general principles of measuring methods.

† IEC 148, Letter symbols for semiconductor devices and integrated microcircuits.

747.7	Bipolar transistors	1.7	Discrete Devices—Bipolar Transistors
747.8	Field-effect transistors	1.8	Discrete Devices—Field-effect Transistors
747.9	Miscellaneous devices	1.9	Discrete Devices—Miscellaneous Devices
747.10	Generic specification for discrete devices and integrated circuits (QC 700 000)	1.10	Generic Specification for Discrete Devices and Integrated Circuits (QC 700 000)
747.11	Sectional specification for discrete devices (QC 750 000)	1.11	Sectional Specification for Discrete Devices (QC 750 000)
IEC 748	Semiconductor Devices. Integrated circuits	AS 2547	Semiconductor Devices.
IEC 748.1	General	2.1	Integrated Circuits—General
IEC 748.2	Digital integrated circuits	2.2	Integrated Circuits—Digital
IEC 748.3	Analogue integrated circuits	2.3	Integrated Circuits—Analogue
IEC 748.4	Interface integrated circuits	2.4	Integrated Circuits—Interface
IEC 749	Semiconductor devices. Mechanical and climatic test methods	3.1	Mechanical and Climatic Test Methods

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## CONTENTS

	Page
CROSS REFERENCE INDEX .....	5
<b>CHAPTER I: GENERAL</b>	
Clause	
1. Introductory note .....	6
2. Scope .....	6
3. Classification .....	6
<b>CHAPTER II: TERMINOLOGY AND LETTER SYMBOLS</b>	
1. Types of field-effect transistors .....	7
2. General terms .....	7
3. Terms related to ratings and characteristics .....	8
4. Letter symbols .....	9
<b>CHAPTER III: ESSENTIAL RATINGS AND CHARACTERISTICS</b>	
1. General .....	15
1.1 Device categories .....	15
1.2 Multiple-gate devices .....	15
1.3 Handling precautions .....	15
2. Ratings (limiting values) .....	15
2.1 Temperatures .....	15
2.2 Power dissipation .....	15
2.3 Voltages and currents .....	15
2.4 Mechanical data .....	16
3. Characteristics .....	16
3.1 Characteristics for low-frequency amplifier applications .....	16
3.2 Characteristics for high-frequency amplifier applications .....	18
3.3 Characteristics for switching applications .....	19
3.4 Characteristics for chopper applications .....	21
3.5 Characteristics for low-level d.c. amplifier applications .....	23
3.6 Characteristics for voltage-controlled resistor applications .....	24
3.7 Specific characteristics of matched-pair field-effect transistors for low-frequency differential applications .....	25
4. Application data .....	26
<b>CHAPTER IV: MEASURING METHODS</b>	
1. General .....	27
1.1 Polarity .....	27
1.2 General precautions .....	27
1.3 Handling precautions .....	27
1.4 Type categories .....	27
2. Gate cut-off current or gate leakage current .....	27
3. Drain current (types A, B and C) .....	29
4. Drain cut-off current (types A, B and C) .....	30
5. Gate-source cut-off voltage (types A and B) .....	30
6. Gate-source threshold voltage (type C) .....	31
7. Small-signal short-circuit input capacitance (types A, B and C) .....	31
8. Small-signal short-circuit output conductance (types A, B and C) .....	33
9. Small-signal short-circuit output capacitance (types A, B and C) .....	35
10. Small-signal short-circuit forward transconductance (types A, B and C) .....	36
11. Small-signal short-circuit feedback capacitance (types A, B and C) .....	39
12. Noise (types A, B and C) .....	41
13. $y$ -parameters (types A, B and C) .....	43
14. Switching times (types A, B and C) .....	43
15. Static drain-source on-state resistance or drain-source on-state voltage and off-state resistance .....	45
16. On-state drain-source resistance (under small-signal conditions) .....	46
17. Scattering parameters .....	47

## CROSS REFERENCES INDEX

New clause number	Old clause number	Document or publication
<i>Chapter I</i>		
1	—	—
2	1.1	147-1, IV
3	4	147-0C, IV
<i>Chapter II</i>		
1 to 2	1 to 2	147-0C, IV
3.1	1.2	147-1, IV
3.2 to 3.7	3.1 to 3.6	147-0C, IV
4.1	—	—
4.2	1.2	} 148, IX 148A, IX
4.3.1 to 4.3.6	3.1 to 3.6	148A, IX
4.3.7	3.7	148B, IX
<i>Chapter III</i>		
1 to 3.6	1 to 3.6	147-1, IV
3.7	3.7	147-1J, IV
4.1	4.1	147-1, IV
<i>Chapter IV</i>		
1 to 16	1 to 16	147-2G, IV
17	17	147-2M, IV

## STANDARDS ASSOCIATION OF AUSTRALIA

**Australian Standard**  
**for**  
**SEMICONDUCTOR DEVICES**

## PART 1.8—DISCRETE DEVICES—FIELD-EFFECT TRANSISTORS

**1. Introductory note**

As a rule, it will be necessary to use Publication 747-1 together with the present publication. In 747-1, the user will find all basic information on:

- terminology;
- letter symbols;
- essential ratings and characteristics;
- measuring methods;
- acceptance and reliability.

The sequence of the different chapters is in accordance with Publication 747-1, Chapter III, Sub-clause 2.1.

**2. Scope**

The present publication gives standards for the following categories of field-effect transistors:

- Type A: junction-gate type;
- Type B: insulated-gate depletion type;
- Type C: insulated-gate enhancement type.

**3. Classification**

Since a field-effect transistor may have one or several gates, the following classification results:

